

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Satoshi MATSUDA, et al.

SERIAL NO: New Application

GAU:

FILED: Herewith

EXAMINER:

FOR: SEMICONDUCTOR DEVICE HAVING SILICIDE FILM AND MANUFACTURING METHOD THEREOF

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references were filed in prior application U.S. Serial No. 10/241,488, filed on September 12, 2002, where required, and were cited and/or made of record in the parent application.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 245583US0S DIV		SERIAL NO. New Application	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Satoshi MATSUDA, et al.			
				FILING DATE Herewith		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	6,518,155	02-03	CHAU, ET AL.			
	AB	6,573,583	06-03	HOKAZONO			
	AC	6,127,707	10-00	CHONG, ET AL.			
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AO	411274320A	10-99	JAPAN			
	AP	2002-110817	04-02	JAPAN			X
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	AW	Yasuhiro SATO, et al., "Study of HF-Treated Heavily-Doped Si Surface Using Contact Angle Measurements", JPN. J. APPL. PHYS., Volume 33, December 1994, Pages 6508-6513.					
	AX	Toshihiko KOSUGI, et al, "Effects of Hydrogenation of Hydrogen Termination of p ⁺ -silicon (100) Surfaces by Hydrofluoric Acid", J. VAC. SCI. TECHNOL. A15(1), Jan/Feb 1997, Pages 127-132.					
	AY	Yoshihiro SUGITA, et al., "Influence of Microscopic Chemical Reactions on the Preparation of an Oxide-Free Silicon Surface in a Fluorine-Based Solution", JPN. J. APPL. PHYS., Volume 38, 1999, Pages 2427-2433.					
	AZ					<input type="checkbox"/> Additional References sheet(s) attached	
Examiner					Date Considered		

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.